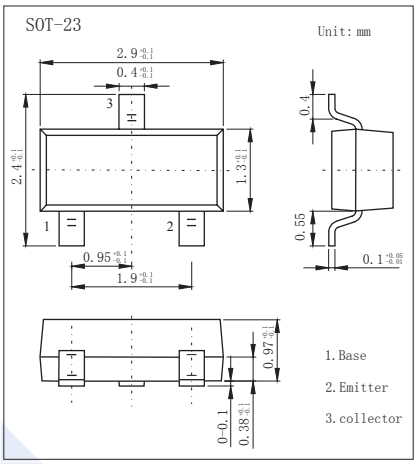
NPN Transistors

2SC2462



■ Features

- Collector Current Capability I_C=100mA
- Collector Emitter Voltage V_{CEO}=40V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	50	V
Collector - Emitter Voltage	V_{CEO}	40	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	100	mA
Emitter Current	I_E	-100	
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 μA, I_E= 0	50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1mA, I_B= 0	40			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 μ A, I_C= 0	5			
Collector-base cut-off current	I_{CBO}	V_{CB}= 30 V , I_E= 0			0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}= 2V , I_C=0			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10mA, I_B=1mA			0.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=10mA, I_B=1mA			1.2	
Base - emitter voltage	V_{BE}	V_{CE}= 12V, I_C=2mA			0.75	
DC current gain	h_{FE}	V_{CE}= 12V, I_C= 2mA	100		500	

■ Classification of h_{fe}

Type	2SC2462-B	2SC2462-C	2SC2462-D
Range	100-200	160-320	250-500
Marking	LB	LC	LD